

ABSTRACT OF THE DISCLOSURE

The resist stripping composition of the present invention comprises 0.001 to 0.5% by weight of a fluorine compound, a mixed solvent of an amide solvent and an ether solvent and water. The resist stripping composition completely
5 removes the resist residues remaining after the dry etching and the ashing in the wiring process for manufacturing semiconductor devices and liquid crystal panel devices comprising IC or LSI in a short period of time with a minimized corrosion of a low dielectric film.